

产品规格书

Specification of products

产品名称: 单相整流桥模块

产品型号: MDQ35A-T11

浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

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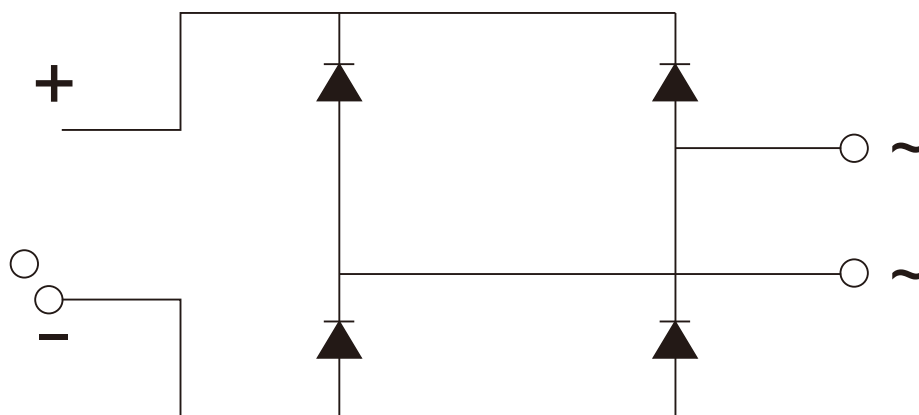
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拟制	审核	核准
林益龙	曹剑龙	宗瑞

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _o	DC output current	Three-phase full wave rectifying circuit, T _c =100 °C	150			35	A
V _{RRM}	Repetitive peak reverse voltage	V _{RRM} tp=10ms V _{RSM} = V _{DRM} &V _{RRM} +200V	150	600		2200	V
I _{RRM}	Repetitive peak current	at V _{RRM}	150			6	mA
I _{FSM}	Surge for ward current	10ms half sine wave	150			0.43	KA
I ² t	I ² T for fusing coordination	V _R =0.6V _{RRM}				1.1	A ² s*10 ³
V _{FO}	Threshold voltage		150			0.80	V
r _F	Forward slop resistance					9.8	mΩ
V _{FM}	Peak for ward voltage	I _{FM} =35A	25			1.1	V
R _{th(j-c)}	Thermal resistance Junction to heatsink	Single side cooled				0.75	°C /W
V _{iso}	Isolation voltage	50Hz, RM. S, t=1min, I _{iso} : 1mA (max)		2500			V
F _m	Terminal connection torque						N.m
	Mounting torque(M4)				3.0		N.m
T _{stg}	Stored temperature			-40		125	°C
W _t	Weight				108		g
Outline							

OUTLINE DR AWING & CIRCUIT DIAGRA M



Rating and Characteristic

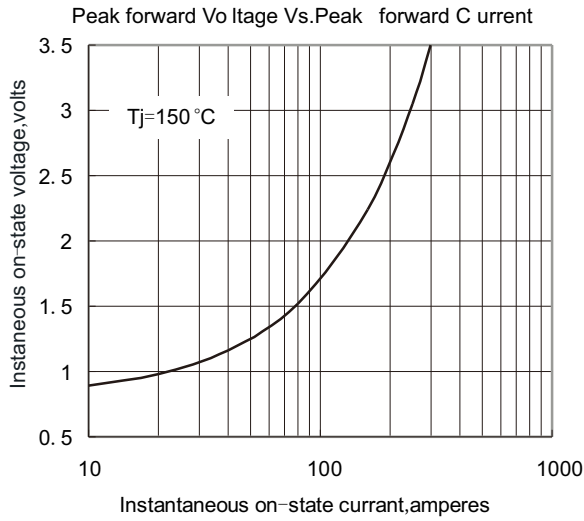


Fig. 1

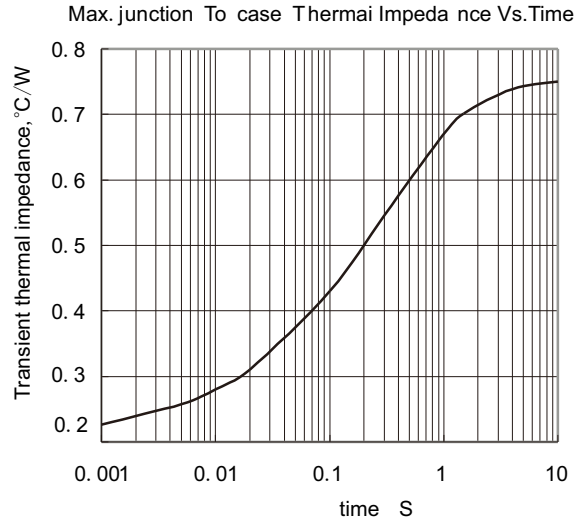


Fig. 2

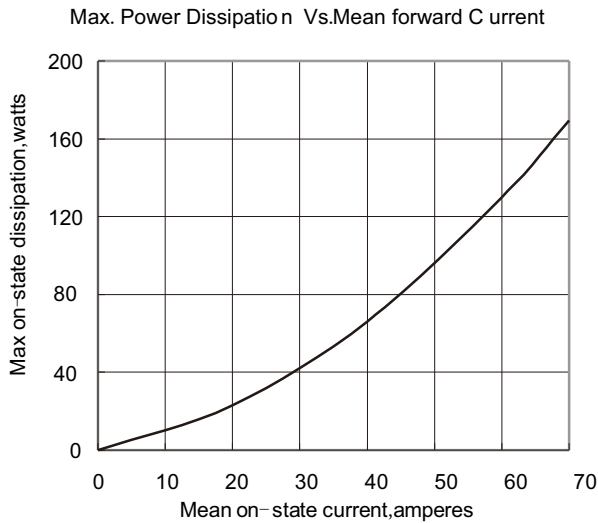


Fig. 3

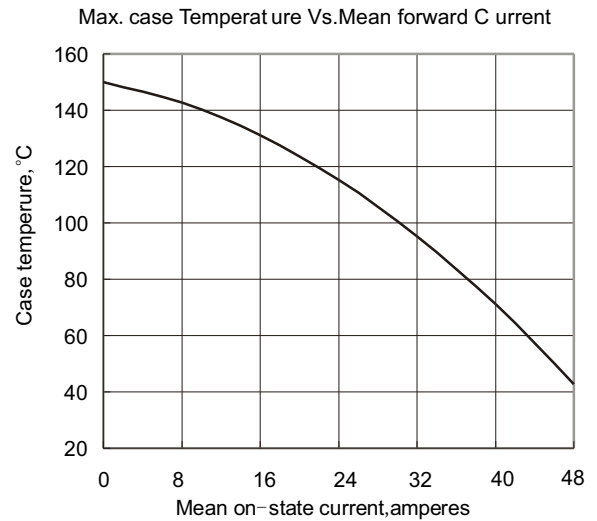


Fig. 4

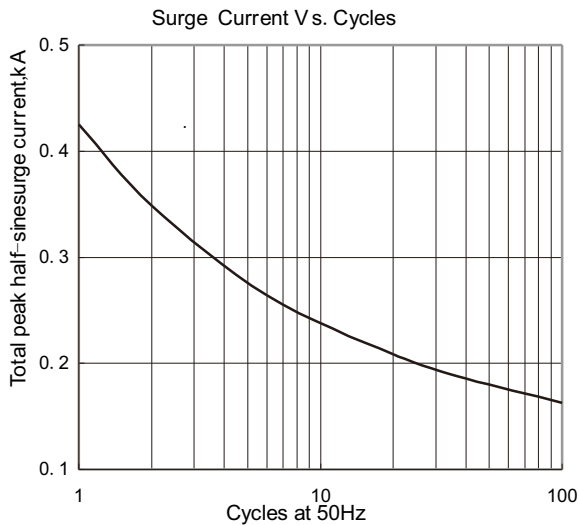


Fig. 5

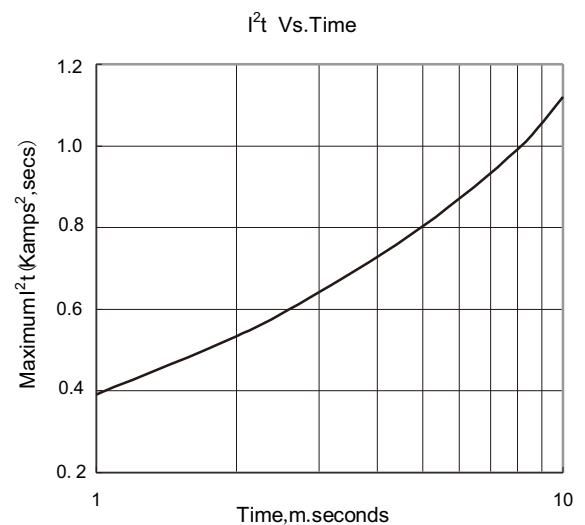


Fig. 6

Outside Dimension

